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Symposium (Oral) | Symposium | III-V semiconductor growth technology for innovative devices

## [8p-A203-1~4]III-V semiconductor growth technology for innovative devices

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Fri. Sep 8, 2017 1:15 PM - 3:15 PM A203 (203)

△：奨励賞エントリー

▲：英語発表

▼：奨励賞エントリーかつ英語発表

空欄：どちらもなし

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2:15 PM - 2:45 PM

## [8p-A203-3]Epitaxial growth on InP template on SiO<sub>2</sub>/Si substrate for fabricating membrane lasers/Si substrate for fabricating membrane lasers

○Shinji Matsuo<sup>1</sup> (1.NTT)

Keywords:InP-based compound semiconductors

We will describe epitaxial growth on InP-based template on SiO<sub>2</sub>/Si substrate, which is an important technology to fabricate large-scale photonic integrated circuits (PICs) with low cost.